SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

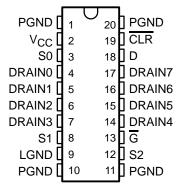
- Low r_{DS(on)} . . . 1.3 Ω Typical
- Avalanche Energy . . . 75 mJ
- Eight Power DMOS Transistor Outputs of 250-mA Continuous Current
- 1.5-A Pulsed Current Per Output
- Output Clamp Voltage at 45 V
- Four Distinct Function Modes
- Low Power Consumption

description

This power logic 8-bit addressable latch controls open-drain DMOS transistor outputs and is designed for general-purpose storage applications in digital systems. Specific uses include working registers, serial-holding registers, and decoders or demultiplexers. This is a multifunctional device capable of storing single-line data in eight addressable latches with 3-to-8 decoding or demultiplexing mode active-low DMOS outputs.

Four distinct modes of operation are selectable by controlling the clear (\overline{CLR}) and enable (\overline{G}) inputs as enumerated in the function table. In the addressable-latch mode, data at the data-in (D) terminal is written into the addressed latch. The addressed DMOS transistor output inverts the data input with all unaddressed DMOS-transistor outputs remaining in their previous states. In the memory mode, all DMOS-transistor outputs remain in their previous states and are unaffected by the data or address inputs. To eliminate the possibility of entering erroneous data in the latch, enable \overline{G} should be held high (inactive) while the address lines are changing. In the 3-to-8 decoding

DW OR N PACKAGE (TOP VIEW)



FUNCTION TABLE

INPUTS		s	OUTPUT OF	EACH	FUNCTION
CLR	G	D	ADDRESSED DRAIN	OTHER DRAIN	FUNCTION
H H	L L	H L	L H	Q _{io} Q _{io}	Addressable Latch
Н	Н	Х	Q _{io}	Q _{io}	Memory
L L	L L	H L	L H	H H	8-Line Demultiplexer
L	Н	Х	Н	Н	Clear

LATCH SELECTION TABLE

SEL	ECT IN	DRAIN	
S2	2 S1	S0	ADDRESSED
L	L	L	0
L	L	Н	1
L	Н	L	2
L	Н	Н	3
Н	L	L	4
Н	L	Н	5
Н	Н	L	6
H	Н	Н	7

or demultiplexing mode, the addressed output is inverted with respect to the D input and all other outputs are high. In the clear mode, all outputs are high and unaffected by the address and data inputs.

Separate power and logic level ground pins are provided to facilitate maximum system flexibility. Pins 1, 10, 11, and 20 are internally connected, and each pin must be externally connected to the power system ground in order to minimize parasitic inductance. A single-point connection between pin 9, logic ground (LGND), and pins 1, 10, 11, and 20, power ground (PGND) must be externally made in a manner that reduces crosstalk between the logic and load circuits.

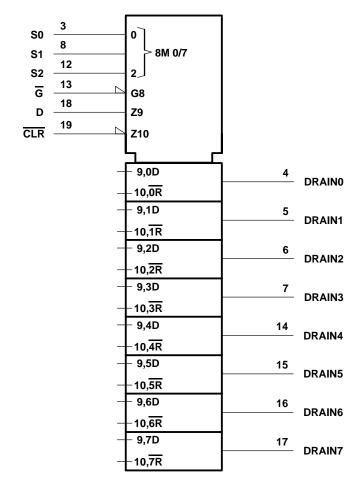
The TPIC6259 is characterized for operation over the operating case temperature range of -40°C to 125°C.



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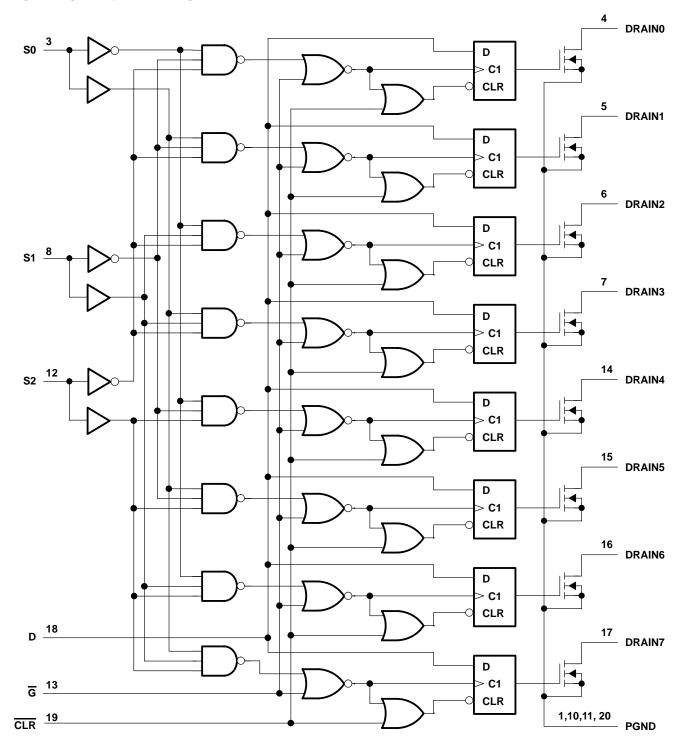


logic symbol†



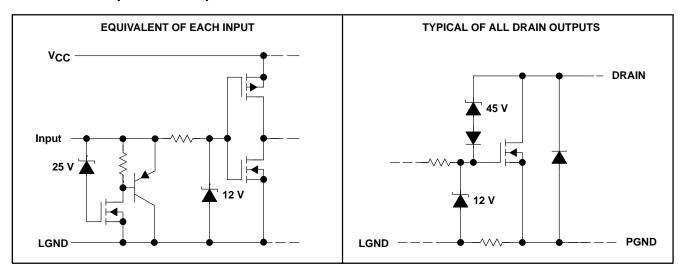
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



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schematic of inputs and outputs



absolute maximum ratings over the recommended operating case temperature range (unless otherwise noted)†

Logic supply voltage, V _{CC} (see Note 1)	
Logic input voltage range, V _I	
Power DMOS drain-to-source voltage, V _{DS} (see Note 2)	45 V
Continuous source-drain diode anode current	1 A
Pulsed source-drain diode anode current	2 A
Pulsed drain current, each output, all outputs on, I_{Dn} , $T_A = 25^{\circ}C$ (see Note 3)	750 mA
Continuous drain current, each output, all outputs on, I_{Dn} , $T_A = 25$ °C	250 mA
Peak drain current single output, I _{DM} , T _A = 25°C (see Note 3)	
Single-pulse avalanche energy, E _{AS} (see Note 4)	
Avalanche current, I _{AS} (see Note 4)	
Continuous total power dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T _J	–40°C to 150°C
Storage temperature range, T _{stg}	
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to LGND and PGND.
 - 2. Each power DMOS source is internally connected to PGND.
 - 3. Pulse duration $\leq 100 \,\mu\text{s}$, duty cycle $\leq 2\%$
 - 4. DRAIN supply voltage = 15 V, starting junction temperature, $(T_{JS}) = 25^{\circ}C$, L = 100 mH, $I_{AS} = 1$ A (see Figure 4).

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \leq 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 125°C POWER RATING
DW	1125 mW	9.0 mW/°C	225 mW
N	1150 mW	9.2 mW/°C	230 mW



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recommended operating conditions over recommended operating temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Logic supply voltage, V _{CC}	4.5	5.5	V
High-level input voltage, V _{IH}	0.85 V _{CC}		V
Low-level input voltage, V _{IL}		0.15 V _{CC}	V
Pulsed drain output current, T _C = 25°C, V _{CC} = 5 V (see Notes 3 and 5)	-1.8	1.5	Α
Setup time, D high before G↑, t _{SU} (see Figure 2)	10		ns
Hold time, D high after G↑, th (see Figure 2)	5		ns
Pulse duration, t _W (see Figure 2)	15		ns
Operating case temperature, T _C	-40	125	°C

electrical characteristics, V_{CC} = 5 V, T_{C} = 25°C (unless otherwise noted)

	PARAMETER		TEST CONDITI	ONS	MIN	TYP	MAX	UNIT
V _{(BR)DSX}	Drain-source breakdown voltage	I _D = 1 mA			45			V
V_{SD}	Source-drain diode forward voltage	$I_F = 250 \text{ mA},$	See Note 3			0.85	1	V
lιΗ	High-level input current	$V_{CC} = 5.5 \text{ V},$	$V_I = V_{CC}$				1	μΑ
I _I L	Low-level input current	$V_{CC} = 5.5 \text{ V},$	V _I = 0				-1	μΑ
ICC	Logic supply current	I _O = 0,	All inputs low			15	100	μΑ
I _N	Nominal current	V _{DS(on)} = 0.5 V _s See Notes 5, 6, 8	$I_N = I_D$, and 7	T _C = 85°C,		250		mA
la ov	Off state desire suggests					0.05	1	^
IDSX	Off-state drain current	$V_{DS} = 40 \text{ V},$	T _C = 125°C			0.15	5	μΑ
		$I_D = 250 \text{ mA},$	V _{CC} = 4.5 V			1.3	2	
r _{DS(on)}	Static drain-source on-state resistance	I _D = 250 mA, V _{CC} = 4.5 V	$T_{C} = 125^{\circ}C,$	See Notes 5 and 6 and Figures 8 and 9		2	3.2	Ω
		I _D = 500 mA,	V _{CC} = 4.5 V]		1.3	2	

switching characteristics, $V_{CC} = 5 \text{ V}$, $T_{C} = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low-to-high-level output from D			625		ns
tPHL	Propagation delay time, high-to-low-level output from D	$C_L = 30 \text{ pF}, \qquad I_D = 250 \text{ mA},$		140		ns
t _r	Rise time, drain output	See Figures 1, 2, and 10		650		ns
t _f	Fall time, drain output			400		ns
ta	Reverse-recovery-current rise time	I _F = 250 mA, di/dt = 20 A/μs,		100		no
t _{rr}	Reverse-recovery time	See Notes 5 and 6 and Figure 3		300		ns

NOTES: 3. Pulse duration $\leq 100 \,\mu\text{s}$, duty cycle $\leq 2\%$

- 5. Technique should limit $T_J T_C$ to 10°C maximum.
- 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- 7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T_C = 85°C.

thermal resistance

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT	
D. The second assistance investigate and investigate		DW package	All C custoute with equal power		111	°C/W
$R_{\theta JA}$	Thermal resistance junction-to-ambient	N package	All 8 outputs with equal power		108	-C/VV



PARAMETER MEASUREMENT INFORMATION

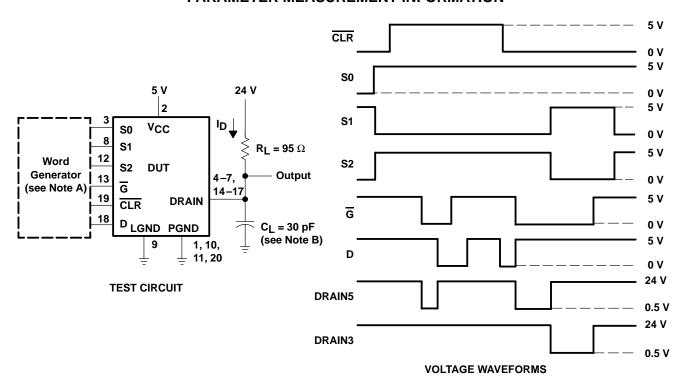


Figure 1. Typical Operation Mode

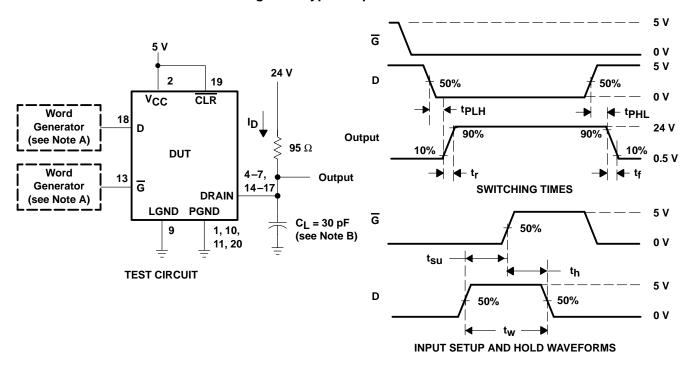


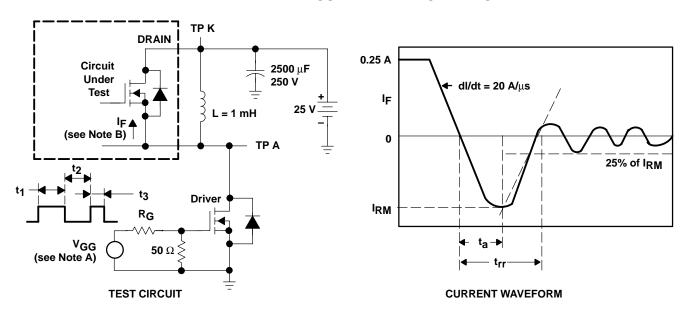
Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

NOTES: A. The word generator has the following characteristics: $t_{\Gamma} \le 10$ ns, $t_{W} = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_{O} = 50 \ \Omega$.

B. C_L includes probe and jig capacitance.

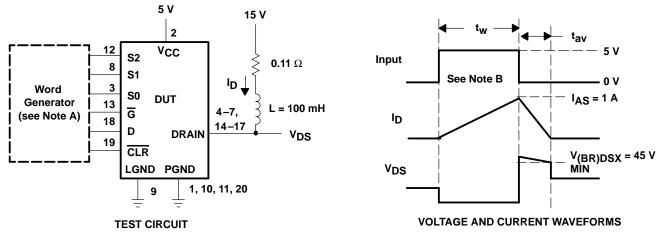


PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The VGG amplitude and RG are adjusted for di/dt = 20 A/ μ s. A VGG double-pulse train is used to set IF = 0.25 A, where t_1 = 10 μ s, t_2 = 7 μ s, and t_3 = 3 μ s.
 - B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

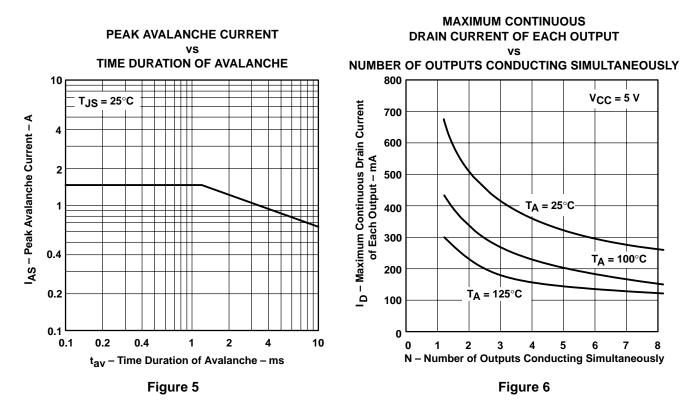
Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode



- NOTES: A. The pulse generator has the following characteristics: $t_r \le 10$ ns, $t_f \le 10$ ns, $z_0 = 50 \ \Omega$.
 - B. Input pulse duration, t_W , is increased until peak current $I_{AS} = 1$ A. Energy test level is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 75$ mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS



MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT vs

NUMBER OF OUTPUTS CONDUCTING SIMULTANEOUSLY

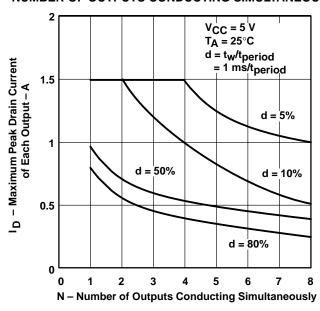


Figure 7

TYPICAL CHARACTERISTICS

STATIC DRAIN-SOURCE ON-STATE RESISTANCE

DRAIN CURRENT <code>rDS(on)</code> – Static Drain-Source On-State Resistance – Ω V_{CC} = 5 V 3.5 See Note A 3 $T_C = 125^{\circ}C$ 2.5 2 $T_C = 25^{\circ}C$ 1.5 1 $T_C = -40^{\circ}C$ 0.5 0.25 0.5 0.75 1.25 1.5 ID - Drain Current - A

STATIC DRAIN-SOURCE ON-STATE RESISTANCE

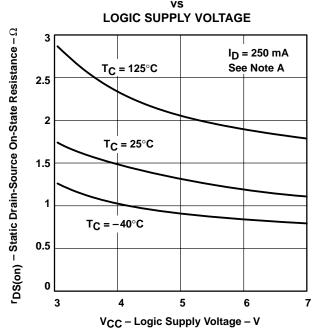


Figure 8 Figure 9

SWITCHING TIME

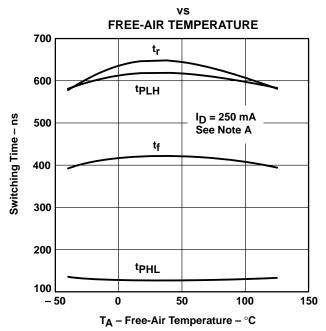


Figure 10

NOTE A: Technique should limit T_J – T_C to 10°C maximum.







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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPIC6259DW	ACTIVE	SOIC	DW	20	25	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6259DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6259DWR	ACTIVE	SOIC	DW	20	2000	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6259DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6259N	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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DW (R-PDSO-G20)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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